

SILICON N-CHANNEL MOS FET

DESCRIPTION:

The **ASI 2SK410** is a silicon n-channel mos fet designed for HF/VHF power amplifier applications.

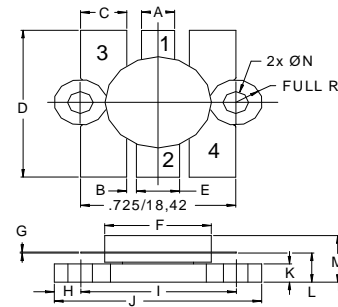
FEATURES:

- $P_G = 17$ dB typ. at 100 W/28 MHz
- **Omnigold™** Metalization System
- Common Source configuration
- RoHS compliant

MAXIMUM RATINGS

I_D	8 A
V_{DSS}	180 V
V_{GSS}	± 20 V
P_{CH}	120 W @ $T_C = 25^\circ C$
T_{CH}	$-55^\circ C$ to $+150^\circ C$
T_{STG}	$-55^\circ C$ to $+150^\circ C$

PACKAGE STYLE .500 6L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.150 / 3.43	.160 / 4.06
B	.045 / 1.14	
C	.210 / 5.33	.220 / 5.59
D	.835 / 21.21	.865 / 21.97
E	.200 / 5.08	.210 / 5.33
F	.490 / 12.45	.510 / 12.95
G	.003 / 0.08	.007 / 0.18
H	.125 / 3.18	
I	.725 / 18.42	
J	.970 / 24.64	.980 / 24.89
K	.090 / 2.29	.105 / 2.67
L	.150 / 3.81	.170 / 4.32
M	.285 / 7.24	
N	.120 / 3.05	.135 / 3.43

1 = COLLECTOR 2 = BASE 3&4 = EMITTER

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$I_C = 100$ mA			180			V
$V_{(BR)GSS}$	$I_G = \pm 100$ μ A	$V_{DS} = 0$ V		± 20			V
$V_{GS(OFF)}$	$I_D = 1.0$ mA	$V_{DS} = 10$ V		0.5		3.0	V
I_{DSS}	$V_{DSS} = 180$ V	$V_{GS} = 0$ V				1.0	mA
$V_{DS(on)}$	$I_D = 4.0$ A	$V_{GS} = 10$ V			3.8	6.0	V
$ y_{fs} $	$I_D = 3.0$ A	$V_{DS} = 20$ V		0.9	1.25		S
C_{ISS}	$V_{GS} = 5.0$ V	$V_{DS} = 0.0$ V	$f = 1.0$ MHz		350		pF
C_{OSS}	$V_{GS} = -5.0$ V	$V_{DS} = 50.$ V	$f = 1.0$ MHz		220		
C_{RSS}	$V_{GS} =$	$V_{GD} = -50.$ V	$f = 1.0$ MHz		15		
P_{OUT}	$V_{DD} = 80$ V $f = 28$ MHz			140			W
η	$I_{DQ} = 100$ mA $P_{IN} = 5$ W				80		%